TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

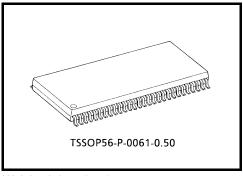
TC74VCX162821FT

Low-Voltage 20-Bit D-Type Flip-Flop with 3.6-V Tolerant Inputs and Outputs

The TC74VCX162821FT is a high-performance CMOS 20-bit D-type flip-flop. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V.$

The device is byte controlled with each byte functioning identically, but independent of the other. Control pins can be shorted together to obtain full 20-bit operation. The following description applies to each byte. The twenty flip-flops will store the state of their individual D inputs that meet the setup and hold time requirements on the LOW-to-HIGH Clock (CK) transition. When the OE input is high, the outputs are in a



Weight: 0.25 g (typ.)

high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The 26- Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

Features

- 26-Ω series resistors on outputs.
- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- High-speed operation: $t_{pd} = 4.4 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V)}$

 $t_{pd} = 5.8 \text{ ns (max) (VCC} = 2.3 \text{ to } 2.7 \text{ V)}$

 $t_{pd} = 9.8 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

• Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $: I_{OH}/I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $: I_{OH}/I_{OL} = \pm 4 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

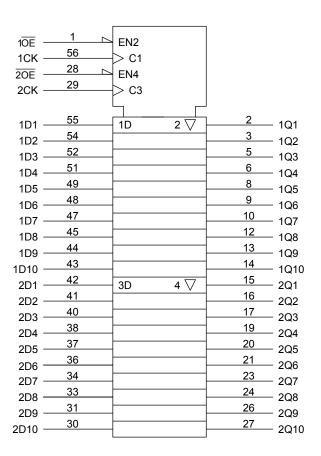
: Human body model $> \pm 2000 \text{ V}$

- Package: TSSOP (thin shrink small outline package)
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Pin Assignment (top view)

10E 1 56 1CK 1Q1 2 55 1D1 1Q2 3 1D2 54 GND 4 **GND** 53 5 1Q3 52 1D3 1Q4 6 51 1D4 V_{CC} 7 50 V_{CC} 1Q5 1D5 8 49 1Q6 9 48 1D6 1Q7 10 1D7 47 GND 11 46 **GND** 1Q8 12 45 1D8 1Q9 13 1D9 1Q10 14 43 1D10 2Q1 15 2D1 42 2Q2 16 41 2D2 2Q3 17 40 2D3 GND 18 **GND** 39 2D4 2Q4 19 38 2Q5 20 37 2D5 2Q6 21 36 2D6 V_{CC} 22 35 Vcc 2Q7 23 34 2D7 2D8 2Q8 24 33 GND 25 **GND** 32 2Q9 26 2D9 31 2D10 2Q10 27 30 2OE 28 2CK 29

IEC Logic Symbol



2 2006-02-01

Truth Table

	Outputs		
1OE	1CK	1D1-1D10	1Q1-1Q10
Н	X	Х	Z
L	\rightarrow	Х	Qn
L		L	L
L		Н	Н

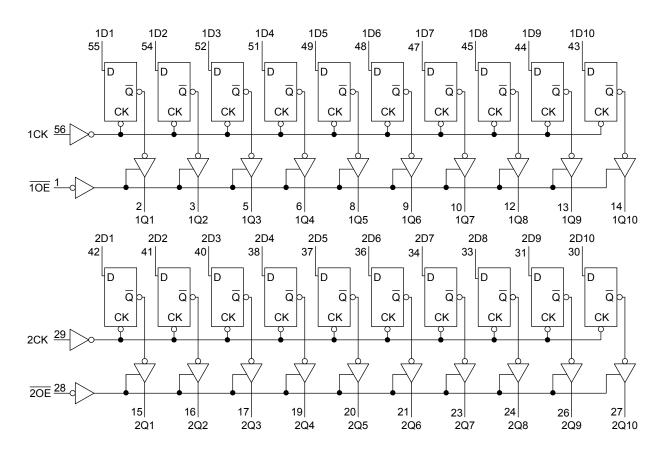
	Outputs		
2 OE	2CK	2D1-2D10	2Q1-2Q10
Н	Х	Х	Z
L	$\overline{}$	Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Qn: No change

System Diagram



3

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: OFF-state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Recommended Operating Range (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	1.8 to 3.6	V	
Tower suppry voltage	VCC	1.2 to 3.6 (Note 2)	V	
Input voltage	V _{IN}	-0.3 to 3.6	V	
Output voltage	Vout	0 to 3.6 (Note 3)	V	
Output voltage	VOU1	0 to V _{CC} (Note 4)	V	
		±12 (Note 5)		
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA	
		±4 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The recommended operating conditions are required to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

Note 3: OFF-state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{\text{CC}} \leq 3.6 \text{ V})$

Characteristics		Symbol	Test (Condition		Min	Max	Unit
		,						
Input voltage	H-level	V _{IH}		_	2.7 to 3.6	2.0	_	V
input voitage	L-level	V _{IL}		_	2.7 to 3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7 to 3.6	V _{CC} - 0.2	_	
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -6 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_	
Output voltage				I _{OH} = -12 mA	3.0	2.2	_	V
		L-level V _{OL}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OL} = 100 μA	2.7 to 3.6	_	0.2	
	L-level			I _{OL} = 6 mA	2.7	_	0.4	
				I _{OL} = 8 mA	3.0	_	0.55	
				I _{OL} = 12 mA	3.0	_	0.8	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μА
2 state subsut OFF sta	4		$V_{IN} = V_{IH}$ or V_{IL}		0.745.0.0		140.0	Δ.
3-state output OFF state current		loz	V _{OUT} = 0 to 3.6 V		2.7 to 3.6	_	±10.0	μА
Power-off leakage current		l _{OFF}	$V_{IN}, V_{OUT} = 0 \text{ to } 3.6$	V	0	_	10.0	μΑ
Quiescent aunaly aurrent		Icc	V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0	
Quiescent supply curre	Quiescent supply current		$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7 to 3.6	_	±20.0	μΑ
Increase in I _{CC} per inp	ut	Δlcc	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	_	750	

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Character	ristics	Symbol	Test	Condition	V _{CC} (V)	Min	Max	Unit	
la a colo collega	H-level	V _{IH}		_	2.3 to 2.7	1.6	_		
Input voltage	L-level	V _{IL}		_	2.3 to 2.7	_	0.7	V	
				I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	_		
	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -4 mA	2.3	2.0	_		
				I _{OH} = -6 mA	2.3	1.8	_	V	
Output voltage				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_		
			V _{OL} V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 100 \mu A$	2.3 to 2.7	_	0.2		
	L-level	V_{OL}		$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3	_	0.6		
Input leakage currer	nt	I _{IN}	V _{IN} = 0 to 3.6 V		2.3 to 2.7	_	±5.0	μА	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.3 to 2.7	_	±10.0	μΑ	
Power-off leakage o	urrent	loff	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μΑ	
		1.	V _{IN} = V _{CC} or GND			_	20.0		
Quiescent supply cu	ırrent	Icc	V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.3 to 2.7	_	±20.0	μΑ	



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test C	condition		Min	Max	Unit
		Cymbol	1631 0	rest Condition		IVIIII	IVICA	Offic
Input voltage	H-level	V _{IH}	-	_	1.8 to 2.3	$\begin{array}{c} 0.7 \times \\ V_{CC} \end{array}$		V
input voltage	L-level	V _{IL}	-	_	1.8 to 2.3	I	0.2 × V _{CC}	V
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -100 \mu A$	1.8	V _{CC} - 0.2	_	
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V
	L-level	Voi	V _{OI} V _{IN} = V _{IH} or V _{II}	$I_{OL} = 100 \mu A$	1.8		0.2	
	L-level	V_{OL} $V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 4 mA	1.8		0.3		
Input leakage current		I _{IN}	$V_{IN} = 0$ to 3.6 V		1.8		±5.0	μΑ
3-state output OFF state current		loz	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \text{ to } 3.6 \text{ V}$		1.8	_	±10.0	μА
Power-off leakage curr	ent	l _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Quioscont supply curro	Outros and records account		V _{IN} = V _{CC} or GND		1.8		20.0	^
Quiescent supply curre	iii.	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8		±20.0	μА

6



AC Characteristics (Ta = –40 to 85°C, input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics	Symbol	Test Condition		Min	Max	Unit
Gridiacteristics	Symbol	rest Condition	V _{CC} (V)	IVIIII	IVIAX	o i i
			1.8	100	_	
Maximum clock frequency	f _{max}	Figure 1, Figure 2	2.5 ± 0.2	200	_	MHz
			3.3 ± 0.3	250	_	
Propagation delay time	.		1.8	1.5	9.8	
(CK-Q)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	5.8	ns
(CK-Q)	t _{pHL}		3.3 ± 0.3	0.6	4.4	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	8.0	5.7	ns
	t _{pZH}		3.3 ± 0.3	0.6	4.2	
	.	Figure 1, Figure 3	1.8	1.5	8.8	
3-state output disable time	t _{pLZ}		2.5 ± 0.2	8.0	4.9	ns
			3.3 ± 0.3	0.6	4.2	
Minimum pulse width	5 a	Figure 1, Figure 2	1.8	4.0	_	
(CK)	tw (H)		2.5 ± 0.2	1.5	_	ns
(OK)	t _{W (L)}		3.3 ± 0.3	1.5	_	
			1.8	2.5	_	
Minimum setup time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
	•		1.8	_	0.5	
Output to output skew	tosLH	(Note 2)	2.5 ± 0.2	_	0.5	ns
	t _{osHL}		3.3 ± 0.3	_	0.5	

Note 1: For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ Ω)

Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Symbol	rest condition	V _{CC} (V)	тур.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	0.15	
Quiet output maximum dynamic V _{OL}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	-0.15	V
Quiet output minimum dynamic VOI	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	-0.25	
, 01		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	-0.35	
Quiet output minimum dynamic V _{OH}		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 1.8	1.55	
	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No	e) 3.3	2.65	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

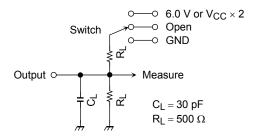
Characteristics	Symbol	Test Condition		Tun	Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	Тур.	Offic
Input capacitance	C _{IN}	_	1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{\text{IN}} = 10 \text{ MHz}$ (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

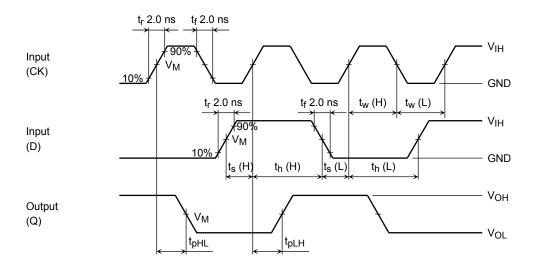


Figure 2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

9

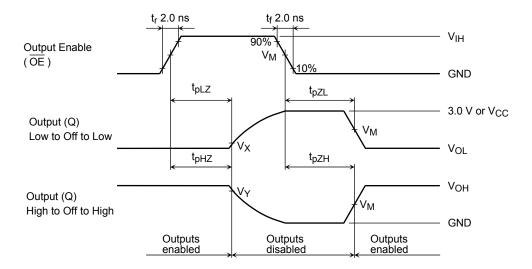
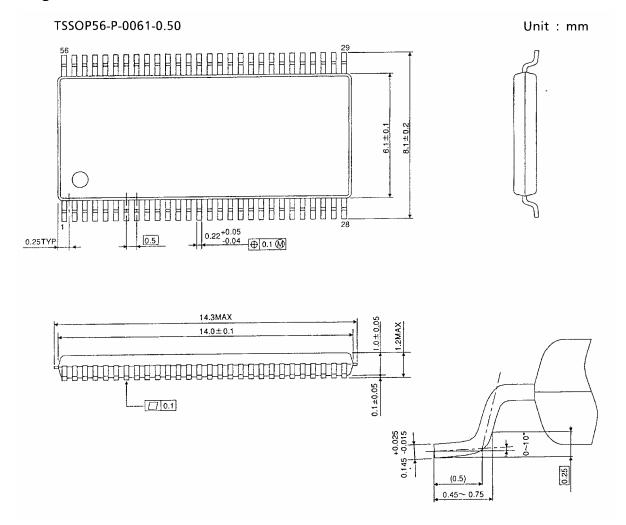


Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Symbol		V _{CC}	
Symbol	$3.3\pm0.3~\textrm{V}$	$2.5\pm0.2\textrm{V}$	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V

10 2006-02-01

Package Dimensions



Weight: 0.25 g (typ.)

Note: Lead (Pb)-Free Packages

TSSOP56-P-0061-0.50

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